

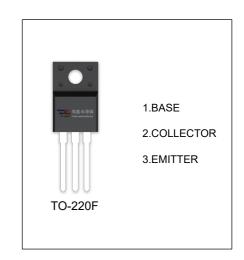
3DD13003F TRANSISTOR (NPN)

FEATURE

Power Switching Applications

MAXIMUM RATINGS (T₂=25 °C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	700	V	
V _{CEO}	Collector-Emitter Voltage	400	V	
V _{EBO}	Emitter-Base Voltage	9	V	
Ic	Collector Current -Continuous	1.5	Α	
Pc	Collector Dissipation	2	W	
R _{θJA}	Thermal Resistance from Junction to Ambient	62.5	°C/W	
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150 ℃		



ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	Ic= 5mA,I _E =0	700			V
Collector-emitter breakdown voltage	V(BR)CEO	V _{(BR)CEO} Ic=10mA,I _B =0				V
Emitter-base breakdown voltage	V(BR)EBO	I _E = 2mA, I _C =0	9			V
Collector cut-off current	I _{CBO}	V _{CB} =700V,I _E =0			1	mA
Collector cut-off current	I _{CEO}	V _{CE} =400V,I _B =0			0.5	mA
Emitter cut-off current	I _{EBO}	V _{EB} =9V, I _C =0			1	mA
DC current gain	h _{FE(1)}	V _{CE} =5V,I _C =0.5 A	8		40	
DC current gam	h _{FE(2)}	V _{CE} =5V,I _C =1.5 A	5			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =1A,I _B =250mA			0.6	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =1A, I _B =250mA			1.2	V
Transition frequency	f _T	V _{CE} =10V,Ic=100mA f =1MHz	5			MHz
Fall time	t _f	I _C =1A,I _{B1} =-I _{B2} =0.2A V _{CC} =100V			0.5	μs
Storage time	t _s	Ic=250mA	2		4	μs

CLASSIFICATION OF h_{FE (1)}

Rank							
Range	8-10	10-15	15-20	20-25	25-30	30-35	35-40

$\textbf{CLASSIFICATION}\,\textbf{OF}\,\,t_{\text{S}}$

Rank	A1	A2	B1	B2
Range	2-2.5 (µs)	2.5-3(µs)	3-3.5(µs)	3.5-4 (µs)